

POSITRONICS OF NANOOBJECTS  
IN POROUS AND DEFECTIVE  
SILICON- AND QUARTZ-BASED SYSTEMS

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S u m m a r y

Positron annihilation spectroscopy (PAS) has been demonstrated to be one of the efficient modern methods for the determination of nanod defect – such as vacancy and vacancy cluster – sizes, the free volume of pores, cavities, and voids, as well as their concentration and chemical composition at annihilation sites in porous systems, some defective materials, and, generally speaking, plenty of technologically important materials and nanomaterials. The results of experimental researches dealing with nanod defects in porous silicon, silicon, single-crystalline quartz, and quartz powders irradiated with protons have been reviewed in brief.